XP-002212231

AN - 2001-053501 [07]
AP - JP19990085182 19990329
CPY - NIHA
DC - L03 M26
FS - CPI
IC - C22C14/00 ; C22C21/00 ; C23C14/34
MC - L04-D02 M26-B09 M26-B09C M26-B09N M26-B09P M26-B09S M26-B09X
PA - (NIHA ) JAPAN ENERGY CORP
PN - JP2000273623 A 20001003 DW200107 C23C14/34 005pp
PR - JP19990085182 19990329
XA - C2001-015256
XIC - C22C-014/00 ; C22C-021/00 ; C23C-014/34
AB - JP2000273623 NOVELTY - A sputtering target contains 5-65 weight% of aluminum, (in ppm) radioactive elements such as uranium and thorium (0.001), alkali metals such as sodium and potassium (0.1), transition metals such as iron (10), nickel (5), cobalt (2) and chromium (2), and other impurities. The sputtering target has purity of 99.995%.
- USE - For formation of barrier film useful for semiconductor device.
- ADVANTAGE - The sputtering target provides a precise film and reduces the generation of pollution substance from the barrier film. The barrier film inhibits the generation of interface state and joining leak by mixing of metal oxide semiconductor (MOS) on radiation and degradation of MOS boundary surface by alkali metal.
- (Dwg.0/0)
IW - TITANIUM ALLOY SPUTTER TARGET USEFUL BARRIER FILM FORMATION SPECIFIC PURE CONTAIN PRESET AMOUNT URANIUM THORIUM SODIUM POTASSIUM IRON NICKEL COBALT CHROMIUM
IKW - TITANIUM ALLOY SPUTTER TARGET USEFUL BARRIER FILM FORMATION SPECIFIC PURE CONTAIN PRESET AMOUNT URANIUM THORIUM SODIUM POTASSIUM IRON NICKEL COBALT CHROMIUM
NC - 001
OPD - 1999-03-29
ORD - 2000-10-03
PAW - (NIHA ) JAPAN ENERGY CORP
TI - Titanium-aluminum alloy sputtering target useful for barrier film formation has specific purity and contains preset amounts of aluminum, uranium and thorium, sodium and potassium, iron, nickel, cobalt and chromium